Ultra-Low Resistance Dual SPDT Analog Switch

The NLAS4685 is an advanced CMOS analog switch fabricated in Sub–micron silicon gate CMOS technology. The device is a dual Independent Single Pole Double Throw (SPDT) switch featuring Ultra–Low R_{ON} of 0.8 $\Omega_{\rm c}$ for the Normally Closed (NC) switch and for the Normally Opened switch (NO) at 2.7 V.

The part also features guaranteed Break Before Make switching, assuring the switches never short the driver.

The NLAS4685 is available in a 2.0 x 1.5 mm bumped die array, with a 3 x 4 arrangement of solder bumps. The pitch of the solder bumps is 0.5 mm for easy handling.

Features

- Ultra–Low R_{ON} , < 0.8 Ω at 2.7 V
- Threshold Adjusted to Function with 1.8 V Control at $V_{CC} = 2.7-3.3 \text{ V}$
- Single Supply Operation from 1.8–5.5 V
- Tiny 2 x 1.5 mm Bumped Die
- Low Crosstalk, < 81 dB at 100 kHz
- Full 0–V_{CC} Signal Handling Capability
- High Isolation, -65 dB at 100 kHz
- Low Standby Current, < 50 nA
- Low Distortion, < 0.14% THD
- R_{ON} Flatness of 0.15 Ω
- Pin for Pin Replacement for MAX4685
- Pb-Free Package is Available

Applications

- Cell Phone
- Speaker Switching
- Power Switching (Up to 100 mA)
- Modems
- Automotive



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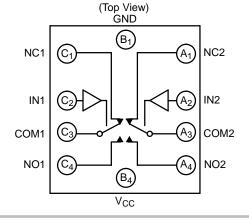
Microbump-10 CASE 489AA



MARKING

XX = Device Code D = Date Code

PIN CONNECTIONS AND LOGIC DIAGRAM



FUNCTION TABLE

IN 1, 2	NO 1, 2	NC 1, 2
0	OFF	ON
1	ON	OFF

ORDERING INFORMATION

Device	Package	Shipping [†]
NLAS4685FCT1	Microbump	3000 Tape/Reel
NLAS4685FCT1G	Microbump (Pb-Free)	3000 Tape/Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	Positive DC Supply Voltage	-0.5 to +7.0	V
V _{IS}	Analog Input Voltage (V _{NO} , V _{NC} , or V _{COM}) (Note 1)	$-0.5 \le V_{IS} \le V_{CC} + 0.5$	V
V _{IN}	Digital Select Input Voltage	$-0.5 \le V_1 \le +7.0$	V
I _{IK}	DC Current, Into or Out of Any Pin	±50	mA

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. Signal voltage on NC, NO, and COM exceeding VCC or GND are clamped by the internal diodes. Limit forward diode current to maximum

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Max	Unit
V _{CC}	DC Supply Voltage		1.8	5.5	V
V _{IN}	Digital Select Input Voltage		GND	5.5	V
V _{IS}	Analog Input Voltage (NC, NO, COM)		GND	V _{CC}	V
T _A	Operating Temperature Range		- 55	+ 125	°C
t _r , t _f	Input Rise or Fall Time, SELECT	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$ $V_{CC} = 5.0 \text{ V} \pm 0.5 \text{ V}$	0	100 20	ns/V

DC CHARACTERISTICS - Digital Section (Voltages Referenced to GND)

				Guaranteed Limit			
Symbol	Parameter	Condition	V _{CC} ±10%	-55°C to 25°C	<85°C	<125°C	Unit
V _{IH}	Minimum High-Level Input		2.0	1.4	1.4	1.4	V
	Voltage, Select Inputs		2.5	1.4	1.4	1.4	
			3.0	1.4	1.4	1.4	
			5.0	2.0	2.0	2.0	
V _{IL}	Maximum Low-Level Input		2.0	0.5	0.5	0.5	V
	Voltage, Select Inputs		2.5	0.5	0.5	0.5	
			3.0	0.5	0.5	0.5	
			5.0	0.8	0.8	0.8	
I _{IN}	Maximum Input Leakage Current, Select Inputs	V _{IN} = 5.5 V or GND	5.5	± 1.0	± 1.0	± 1.0	μΑ
I _{OFF}	Power Off Leakage Current	V _{IN} = 5.5 V or GND	0	±10	±10	± 10	μΑ
Icc	Maximum Quiescent Supply Current	Select and V _{IS} = V _{CC} or GND	5.5	± 180	± 200	± 200	nA

current rating.

DC ELECTRICAL CHARACTERISTICS - Analog Section

					Guarant	eed Ma	ximum	Limit		
				-55°C	to 25°C	<8	5°C	<12	25°C	
Symbol	Parameter	Condition	V _{CC} ±10%	Min	Max	Min	Max	Min	Max	Unit
R _{ON} (NC, NO)	"ON" Resistance (Note 2)	$\begin{split} &V_{IN} \geq V_{IH} \\ &V_{IS} = GND \text{ to } V_{CC} \\ &I_{IN}I \leq 100 \text{ mA} \end{split}$	2.5 3.0 5.0		2.0 0.8 0.8		2.0 0.8 0.8		2.0 1.0 0.9	Ω
R _{FLAT} (NC, NO)	On–Resistance Flatness (Notes 2, 4)	I _{COM} = 100 mA V _{IS} = 0 to V _{CC}	2.5 3.0 5.0		0.35 0.35 0.35		0.35 0.35 0.35		0.35 0.35 0.35	Ω
ΔR _{ON}	On–Resistance Match Between Channels (Notes 2 and 3)	$V_{IS} = 1.3 \text{ V};$ $I_{COM} = 100 \text{ mA}$ $V_{IS} = 1.5 \text{ V};$ $I_{COM} = 100 \text{ mA}$ $V_{IS} = 2.8 \text{ V};$ $I_{COM} = 100 \text{ mA}$	2.5 3.0 5.0		0.18 0.06 0.06		0.18 0.06 0.06		0.18 0.06 0.06	Ω
I _{NC(OFF)} I _{NO(OFF)}	NC or NO Off Leakage Current (Figure 10)	$\begin{aligned} V_{IN} &= V_{IL} \text{ or } V_{IH} \\ V_{NO} \text{ or } V_{NC} &= 1.0 \\ V_{COM} &= 4.5 \text{ V} \end{aligned}$	5.5	-1	1	-10	10	-150	150	nA
I _{COM(ON)}	COM ON Leakage Current (Figure 10)	$\begin{aligned} &V_{IN} = V_{IL} \text{ or } V_{IH} \\ &V_{NO} \text{ 1.0 V or 4.5 V with} \\ &V_{NC} \text{ floating or} \\ &V_{NC} \text{ 1.0 V or 4.5 V with} \\ &V_{NO} \text{ floating} \\ &V_{COM} = 1.0 \text{ V or 4.5 V} \end{aligned}$	5.5	-1	1	-10	10	-150	150	nA

Guaranteed by design. Resistance measurements do not include test circuit or package resistance.

 \[\Delta R_{ON} = R_{ON(MAX)} - R_{ON(MIN)} \]
 between all switches.

 Flatness is defined as the difference between the maximum and minimum value of on-resistance as measured over the specified analog signal ranges.

AC ELECTRICAL CHARACTERISTICS (Input $t_{\text{f}} = t_{\text{f}} = 3.0 \text{ ns}$)

			Guaranteed Maximum Limit									
			v _{cc}	V _{IS}	-5	5°C to 2	25°C	<8	5°C	<12	25°C	
Symbol	Parameter	Test Conditions	(V)	(V)	Min	Тур*	Max	Min	Max	Min	Max	Unit
t _{ON}	Turn-On Time	$R_L = 50 \Omega, C_L = 35 pF$	2.5	1.3			55		65		70	ns
		(Figures 2 and 3)	3.0	1.5			50		60		60	
			5.0	2.8			30		35		35	
t _{OFF}	Turn-Off Time	$R_L = 50 \Omega, C_L = 35 pF$	2.5	1.3			55		65		70	ns
		(Figures 2 and 3)	3.0	1.5			50		60		60	
			5.0	2.8			25		30		30	
t _{BBM}	Minimum Break-Before-Make Time	V_{IS} = 3.0 R_L = 300 Ω , C_L = 35 pF (Figure 1)	3.0	1.5	2	15						ns

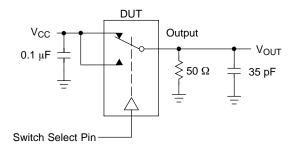
		Typical @ 25, V _{CC} = 5.0 V	V _{CC} = 3.0 V	
C _{NC} Off C _{NO} Off C _{NC} On C _{NO} On	NC Off Capacitance, f = 1 MHz NO Off Capacitance, f = 1 MHz NC On Capacitance, f = 1 MHz NO On Capacitance, f = 1 MHz		208 102 547 431	pF

^{*}Typical Characteristics are at 25°C.

ADDITIONAL APPLICATION CHARACTERISTICS (Voltages Referenced to GND Unless Noted) (Note 6)

			V _{CC}	Typical	
Symbol	Parameter	Condition	V	25°C	Unit
BW	Maximum On–Channel –3dB Bandwidth or Minimum Frequency Response	V_{IN} = 0 dBm NC/NO V_{IN} centered between V_{CC} and GND (Figure 4)	3.0	11.5	MHz
V _{ONL}	Maximum Feed-through On Loss	V_{IN} = 0 dBm @ 100 kHz to 50 MHz V_{IN} centered between V_{CC} and GND (Figure 4)	3.0	-0.05	dB
V _{ISO}	Off-Channel Isolation	$f = 100 \text{ kHz}$; $V_{IS} = 1 \text{ V RMS}$; $C_L = 5 \text{ nF}$ V_{IN} centered between V_{CC} and GND(Figure 4)	3.0	-65	dB
Q	Charge Injection Select Input to Common I/O	$V_{IN} = V_{CC to}$ GND, $R_{IS} = 0 \Omega$, $C_L = 1 nF$ $Q = C_L - \Delta V_{OUT}$ (Figure 5)	3.0 5.0	15 20	рС
THD	Total Harmonic Distortion THD + Noise	F_{IS} = 20 Hz to 20 kHz, R_L = R_{gen} = 600 Ω , C_L = 50 pF V_{IS} = 1 V RMS	3.0	0.14	%
VCT	Channel-to-Channel Crosstalk	f = 100 kHz; V_{IS} = 1 V RMS, C_L = 5 pF, R_L = 50 Ω V_{IN} centered between V_{CC} and GND (Figure 4)	3.0	-81	dB

^{5.} Off–Channel Isolation = 20log10 (Vcom/Vno), Vcom = output, Vno = input to off switch. 6. -40° C specifications are guaranteed by design.



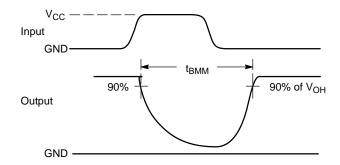
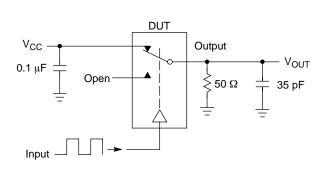


Figure 1. t_{BBM} (Time Break-Before-Make)



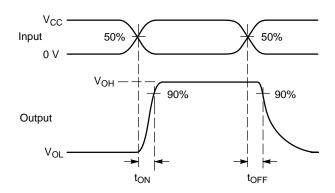
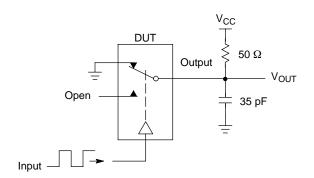


Figure 2. t_{ON}/t_{OFF}



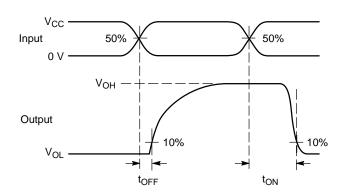
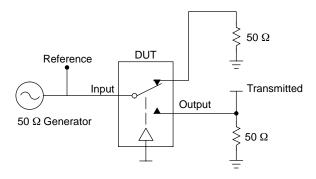


Figure 3. t_{ON}/t_{OFF}



Channel switch control/s test socket is normalized. Off isolation is measured across an off channel. On loss is the bandwidth of an On switch. $V_{\rm ISO}$, Bandwidth and $V_{\rm ONL}$ are independent of the input signal direction.

$$\begin{split} &V_{ISO} = \text{Off Channel Isolation} = 20 \text{ Log} \left(\frac{V_{OUT}}{V_{IN}} \right) \text{ } \text{ for } V_{IN} \text{ at } 100 \text{ kHz} \\ &V_{ONL} = \text{On Channel Loss} = 20 \text{ Log} \left(\frac{V_{OUT}}{V_{IN}} \right) \text{ } \text{ for } V_{IN} \text{ at } 100 \text{ kHz to } 50 \text{ MHz} \end{split}$$

Bandwidth (BW) = the frequency 3 dB below V_{ONL}

 V_{CT} = Use V_{ISO} setup and test to all other switch analog input/outputs terminated with 50 Ω

Figure 4. Off Channel Isolation/On Channel Loss (BW)/Crosstalk (On Channel to Off Channel)/V_{ONL}

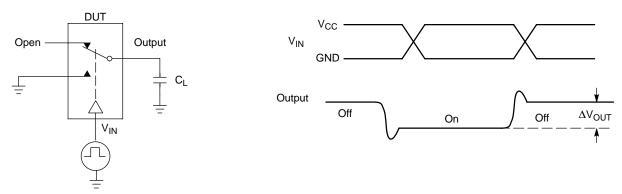
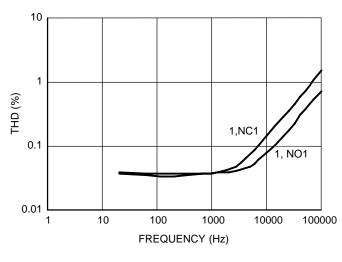


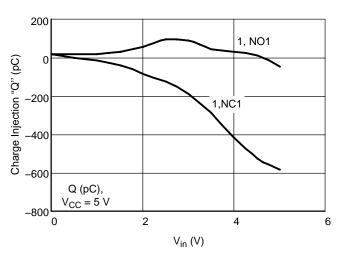
Figure 5. Charge Injection: (Q)



1.6 1.4 Threshold Rising 1.2 Vin THRESHOLD (V) 1 Threshold Falling 0.8 0.6 0.4 0.2 0 0 2 4 6 $V_{CC}(V)$

Figure 6. Total Harmonic Distortion Plus Noise versus Frequency

Figure 7. Voltage in Threshold on Logic Pins



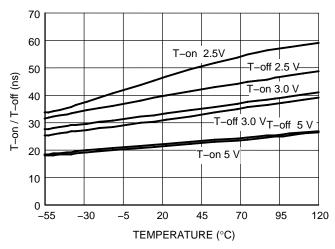


Figure 8. Charge Injection versus V_{is}

Figure 9. T-on/T-off Time versus Temperature

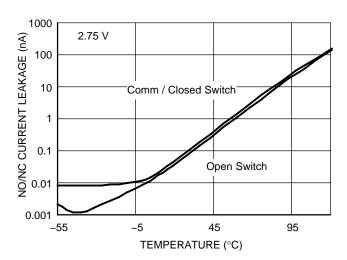


Figure 10. NO/NC Current Leakage Off and On, $V_{CC} = 5 \text{ V}$

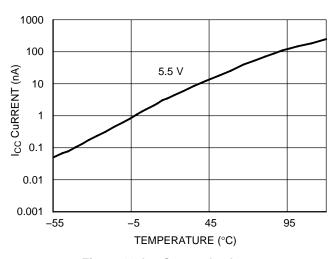


Figure 11. I_{CC} Current Leakage versus Temperature V_{CC} = 5.5 V

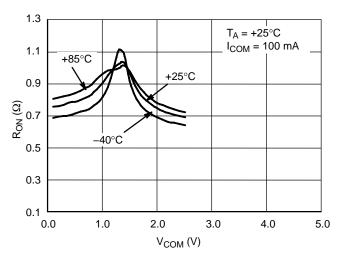


Figure 12. NC/NO On–Resistance versus COM Voltage

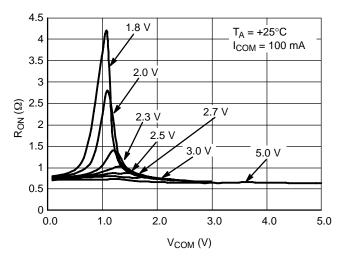


Figure 13. NC/NO On–Resistance versus COM Voltage

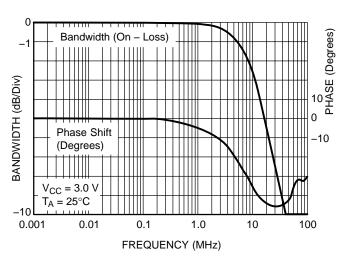


Figure 14. NC/NO Bandwidth and Phase Shift versus Frequency

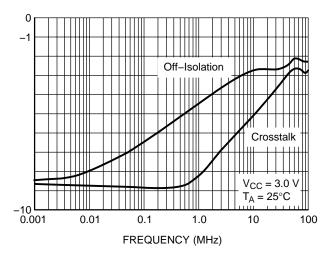
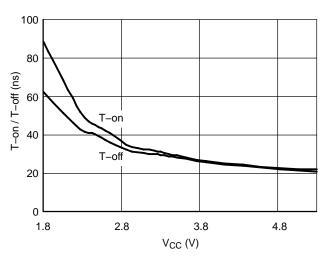


Figure 15. NC/NO Off Isolation and Crosstalk



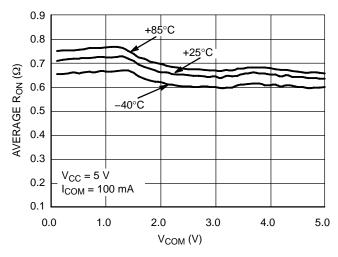


Figure 16. T-on/T-off versus V_{CC}

Figure 17. NC/NO On–Resistance versus COM Voltage

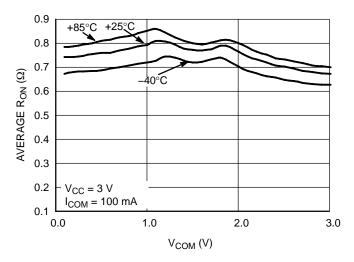


Figure 18. NC/NO On-Resistance versus COM Voltage

DATE 04 MAY 2004



10 PIN FLIP-CHIP CASE 489AA-01



SCALE 4:1

ISSUE A

NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. 2. CONTROLLING DIMENSION:
- MILLIMETERS. COPLANARITY APPLIES TO SPHERICAL CROWNS OF SOLDER BALLS.

	MILLIMETERS				
DIM	MIN	MAX			
Α		0.650			
A1	0.210	0.270			
A2	0.280	0.380			
D	1.965	BSC			
Е	1.465	BSC			
b	0.250	0.350			
е	0.500 BSC				
D1	1.500 BSC				
E1	1.000	BSC			

GENERIC MARKING DIAGRAM*

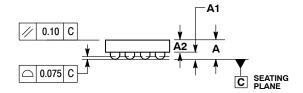


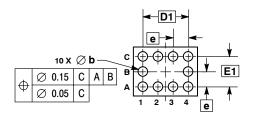
= Specific Device Code XXXX

ΥY = Year WW = Work Week

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

4 X	← D→	A B
□ 0.10 C		T
PIN ONE CORNER	P	





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